

## 英飞凌OptiMOS™-T 功率晶体管



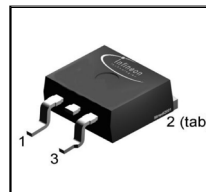
### Product Summary

|                                |     |    |
|--------------------------------|-----|----|
| $V_{DS}$                       | 100 | V  |
| $R_{DS(on),max}$ (SMD version) | 4.8 | mW |
| $I_D$                          | 100 | A  |

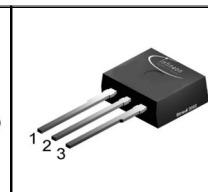
### 特性

- N 沟道-增强型
- 符合汽车级 AEC Q101 标准
- MSL1 回流焊峰值温度高达 260°C
- 工作温度 175°C
- 符合 RoHS 标准
- 100% 雪崩测试

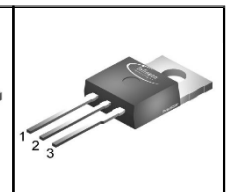
PG-T0263-3-2



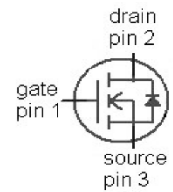
PG-T0262-3-1



PG-T0220-3-1



| Type           | Package      | Marking |
|----------------|--------------|---------|
| IPB100N10S3-05 | PG-T0263-3-2 | 3PN1005 |
| IPI100N10S3-05 | PG-T0262-3-1 | 3PN1005 |
| IPP100N10S3-05 | PG-T0220-3-1 | 3PN1005 |



除非另有规定，否则均为  $T_j=25\text{ °C}$  的**最大额定值**

| Parameter                                    | Symbol         | Conditions                                   | Value        | Unit |
|----------------------------------------------|----------------|----------------------------------------------|--------------|------|
| Continuous drain current <sup>1)</sup>       | $I_D$          | $T_c=25\text{ °C}, V_{GS}=10\text{ V}$       | 100          | A    |
|                                              |                | $T_c=100\text{ °C}, V_{GS}=10\text{ V}^{2)}$ | 100          |      |
| Pulsed drain current <sup>2)</sup>           | $I_{D,pulse}$  | $T_c=25\text{ °C}$                           | 400          |      |
| Avalanche energy, single pulse <sup>2)</sup> | $E_{AS}$       | $I_D=50\text{ A}$                            | 1445         | mJ   |
| Avalanche current, single pulse              | $I_{AS}$       |                                              | 100          | A    |
| Gate source voltage                          | $V_{GS}$       |                                              | ±20          | V    |
| Power dissipation                            | $P_{tot}$      | $T_c=25\text{ °C}$                           | 300          | W    |
| Operating and storage temperature            | $T_j, T_{stg}$ |                                              | -55 ... +175 | °C   |
| IEC climatic category; DIN IEC 68-1          |                |                                              | 55/175/56    |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### 热特性<sup>2)</sup>

|                                                |            |                                              |   |   |     |     |
|------------------------------------------------|------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case            | $R_{thJC}$ |                                              | - | - | 0.5 | K/W |
| Thermal resistance, junction - ambient, leaded | $R_{thJA}$ |                                              | - | - | 62  |     |
| SMD version, device on PCB                     | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|                                                |            | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | - | - | 40  |     |

电气特性，除非另有规定，否则均为  $T_j=25\text{ °C}$

### 静态特性

|                                  |               |                                                                 |     |      |     |               |
|----------------------------------|---------------|-----------------------------------------------------------------|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(Br)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                            | 100 | -    | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=240\mu\text{A}$                             | 2.0 | 3.0  | 4.0 |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$       | -   | 0.01 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=80\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}^{2)}$ | -   | 1    | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{V}, V_{DS}=0\text{V}$                           | -   | -    | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{V}, I_D=100\text{A}$                            | -   | 4.3  | 5.1 | mW            |
|                                  |               | $V_{GS}=10\text{V}, I_D=100\text{A},$<br>SMD version            | -   | 4.0  | 4.8 |               |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

### 动态特性<sup>2)</sup>

|                              |              |                                                  |   |      |       |    |
|------------------------------|--------------|--------------------------------------------------|---|------|-------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0V, V_{DS}=25V,$<br>$f=1MHz$             | - | 8900 | 11570 | pF |
| Output capacitance           | $C_{oss}$    |                                                  | - | 2520 | 3276  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                  | - | 220  | 330   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=20V, V_{GS}=10V,$<br>$I_D=80A, R_G=3.5W$ | - | 34   | -     | ns |
| Rise time                    | $t_r$        |                                                  | - | 17   | -     |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                  | - | 60   | -     |    |
| Fall time                    | $t_f$        |                                                  | - | 20   | -     |    |

### 栅极电荷特性<sup>2)</sup>

|                       |               |                                                       |   |     |     |    |
|-----------------------|---------------|-------------------------------------------------------|---|-----|-----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=80V, I_D=100A,$<br>$V_{GS}=0 \text{ to } 10V$ | - | 47  | 61  | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                       | - | 34  | 51  |    |
| Gate charge total     | $Q_g$         |                                                       | - | 135 | 176 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                       | - | 5.5 | -   | V  |

### 反向二极管

|                                                |               |                                             |     |     |     |    |
|------------------------------------------------|---------------|---------------------------------------------|-----|-----|-----|----|
| Diode continuous forward current <sup>2)</sup> | $I_s$         | $T_C=25^\circ C$                            | -   | -   | 100 | A  |
| Diode pulse current <sup>2)</sup>              | $I_{S,pulse}$ |                                             | -   | -   | 400 |    |
| Diode forward voltage                          | $V_{SD}$      | $V_{GS}=0V, I_F=80A,$<br>$T_j=25^\circ C$   | 0.6 | 1   | 1.2 | V  |
| Reverse recovery time <sup>2)</sup>            | $t_{rr}$      | $V_R=50V, I_F=I_s,$<br>$di_F/dt=100A/\mu s$ | -   | 108 | -   | ns |
| Reverse recovery charge <sup>2)</sup>          | $Q_{rr}$      |                                             | -   | 380 | -   | nC |

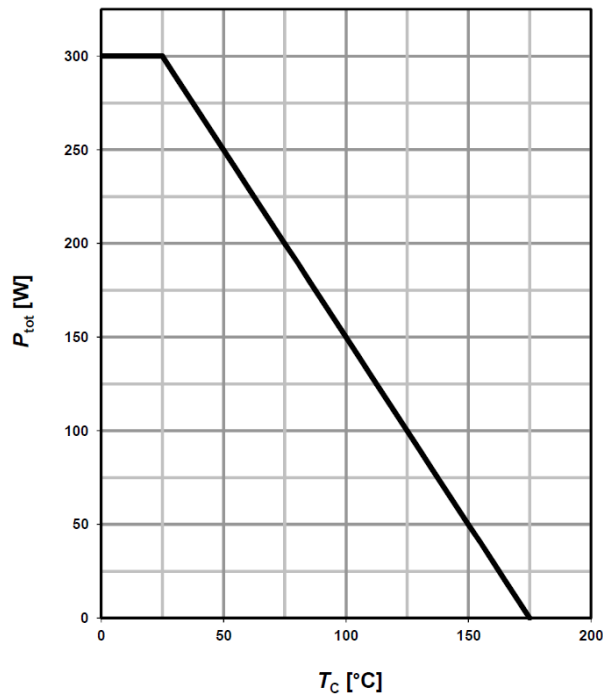
<sup>1)</sup> 电流受到接合线的限制；当  $R_{thJC} = 0.5K/W$  时，芯片能够在  $25^\circ C$  时承载 165A。有关详细信息，请参阅应用注释 ANPS071E，网址：[www.infineon.com/optimos](http://www.infineon.com/optimos)

<sup>2)</sup> 由设计指定，未经过生产测试。

<sup>3)</sup> 器件置于  $40mm \times 40mm \times 1.5mm$  环氧树脂印刷电路板 FR4 上，配有  $6cm^2$ （一层， $70\mu m$  厚）铜层面积用于漏极连接。印刷电路板在静止空气中垂直放置。

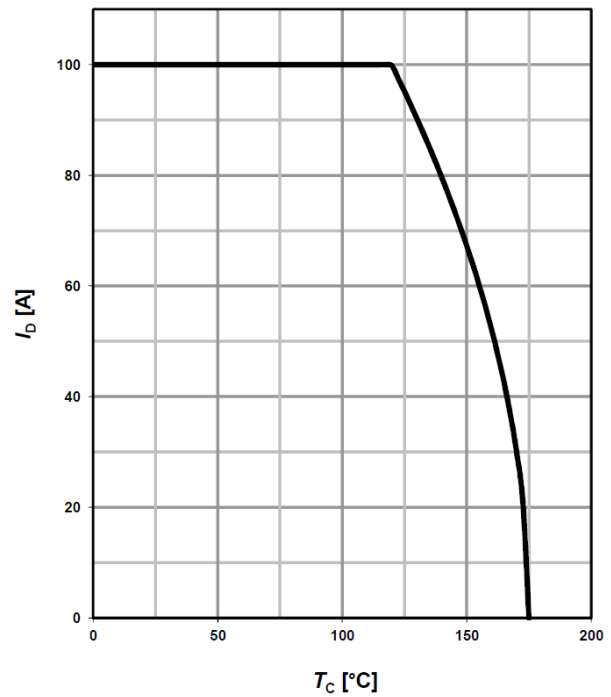
## 1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



## 2 Drain current

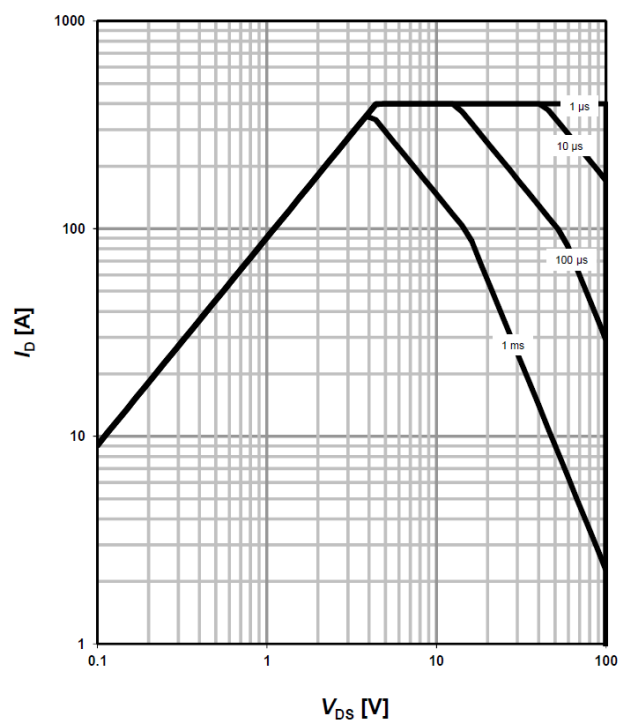
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}; \text{SMD}$$



## 3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0; \text{SMD}$$

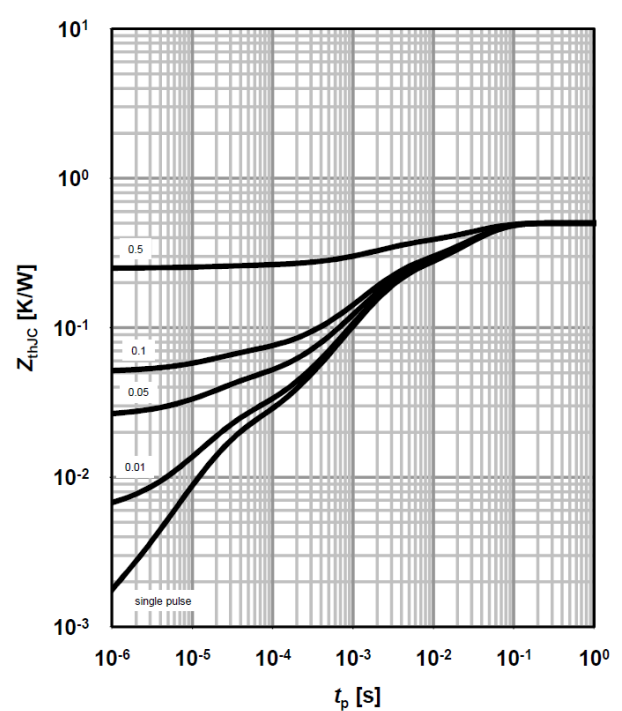
parameter:  $t_p$



## 4 Max. transient thermal impedance

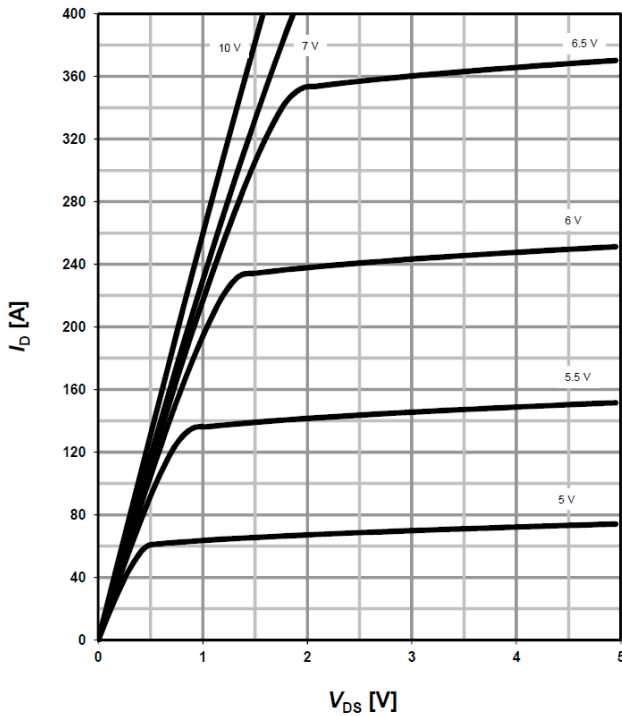
$$Z_{\text{thJC}} = f(t_p)$$

parameter:  $D = t_p/T$



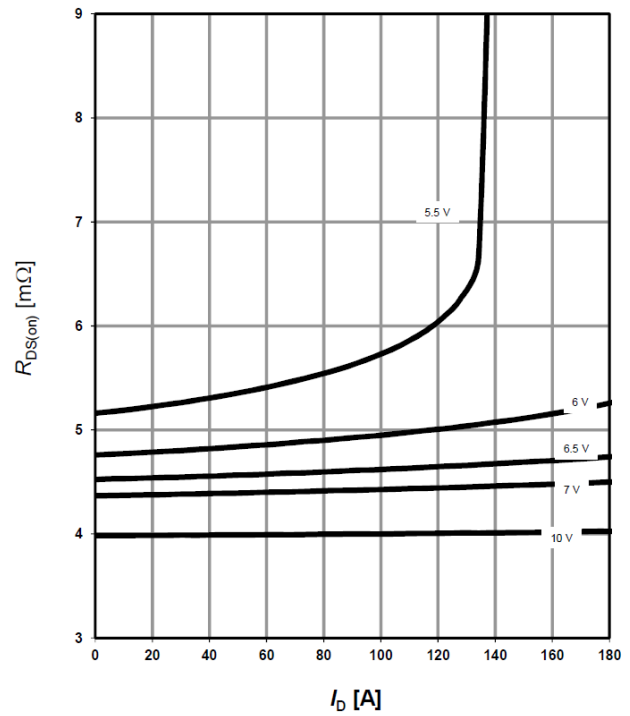
### 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{SMD}$ 

parameter:  $V_{GS}$ 


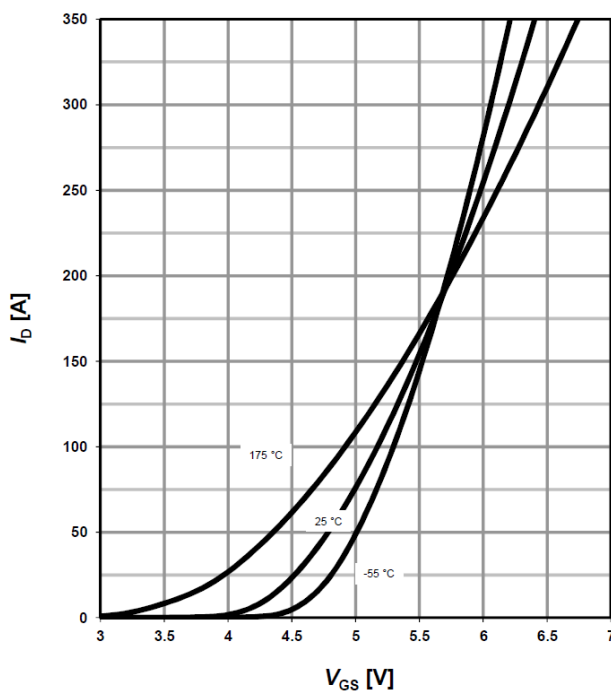
### 6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}; \text{SMD}$ 

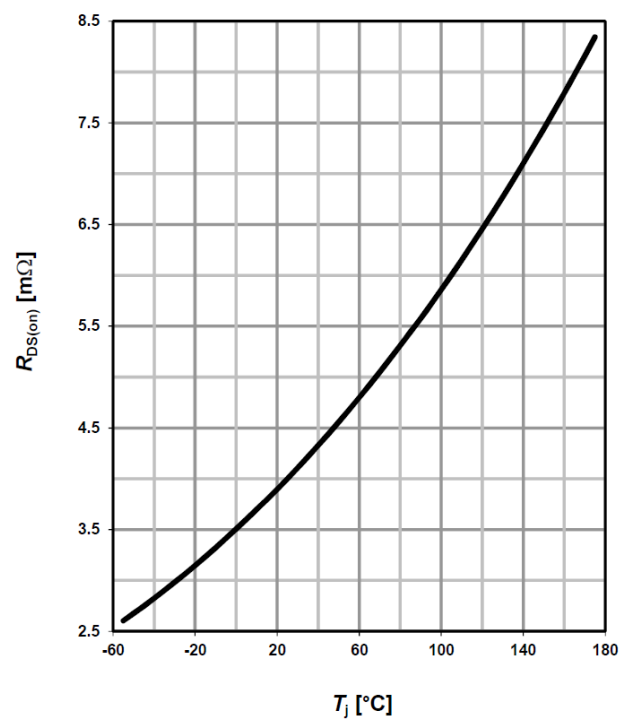
parameter:  $V_{GS}$ 


### 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = 6\text{V}$ 

parameter:  $T_j$ 


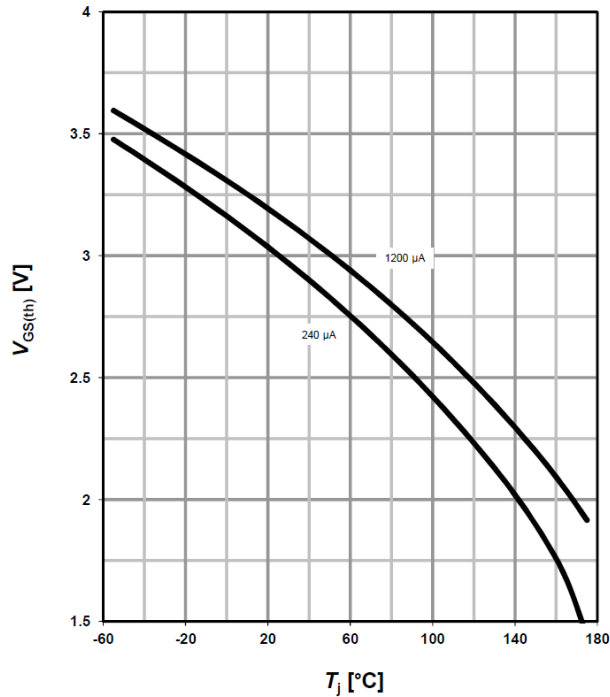
### 8 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = 100\text{ A}; V_{GS} = 10\text{ V}; \text{SMD}$ 
 $\alpha = 0.56$ 


### 9 Typ. gate threshold voltage

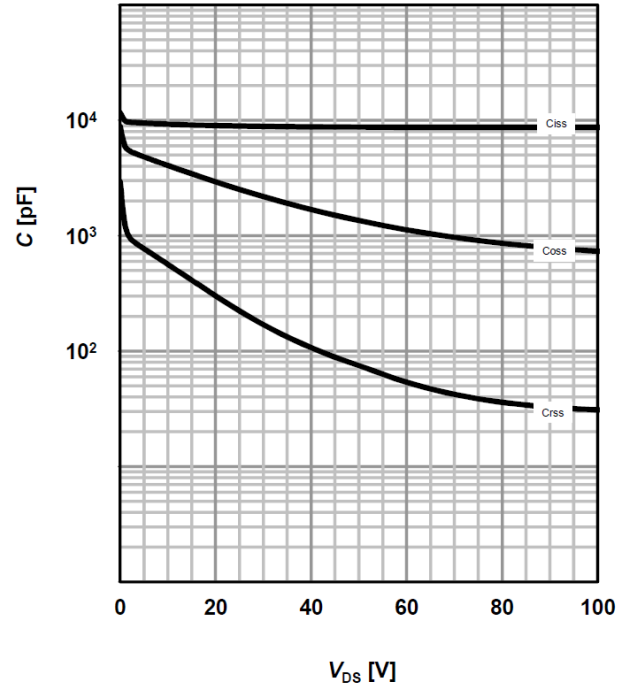
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



### 10 Typ. capacitances

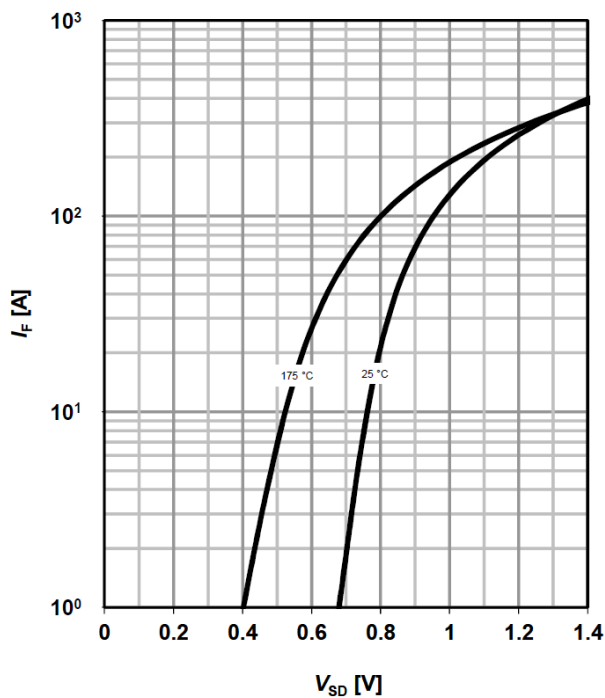
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



### 11 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

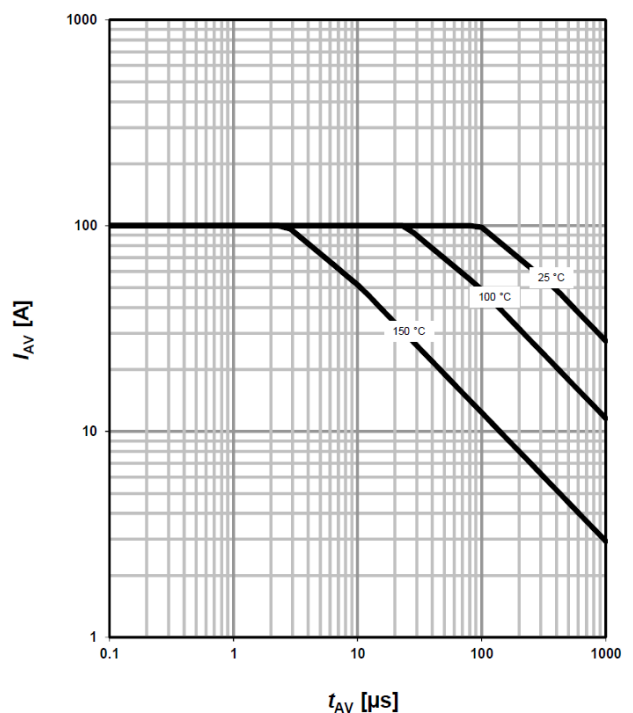
parameter:  $T_j$



### 12 Typ. avalanche characteristics

$$I_{AS} = f(t_{AV})$$

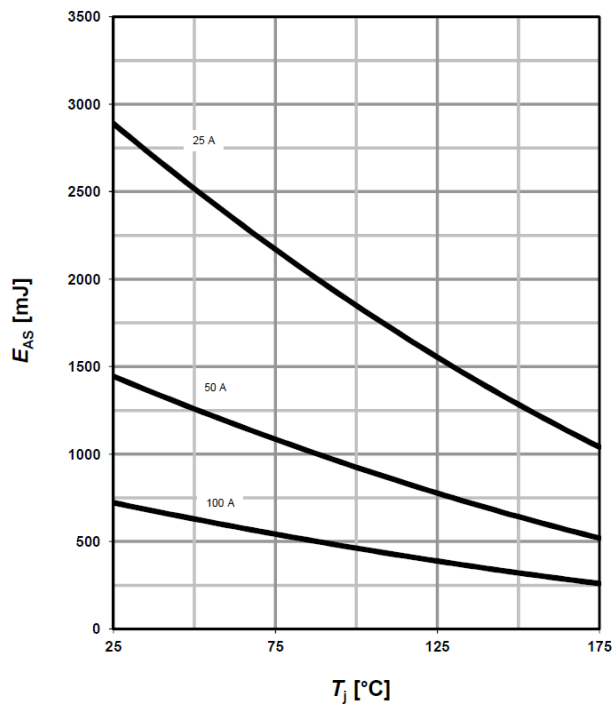
parameter:  $T_{j(start)}$



### 13 Typical avalanche energy

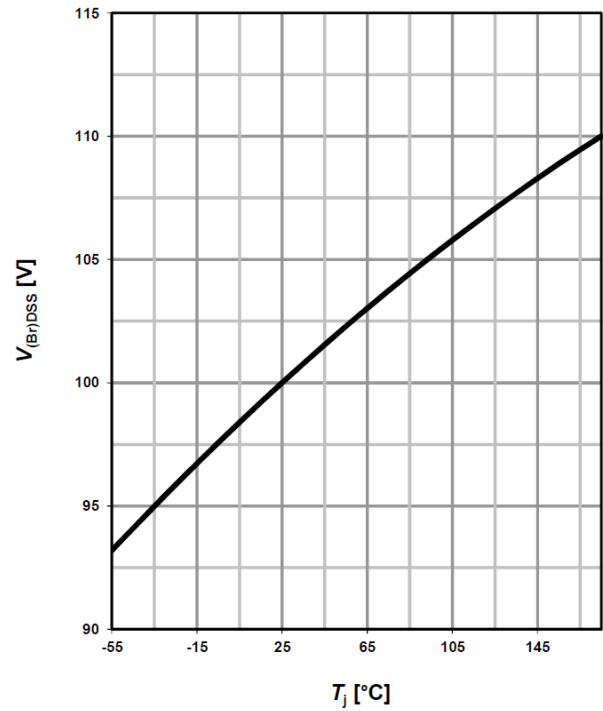
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



### 14 Typ. drain-source breakdown voltage

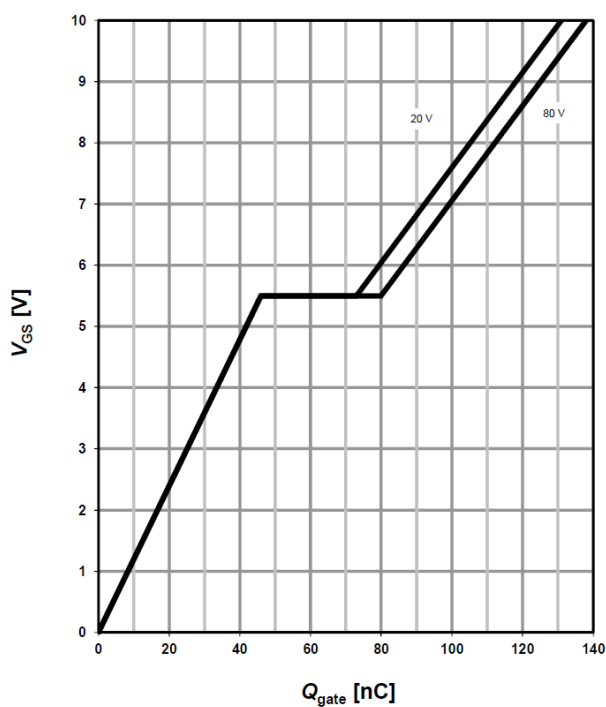
$$V_{(Br)DSS} = f(T_j); I_D = 1 \text{ mA}$$



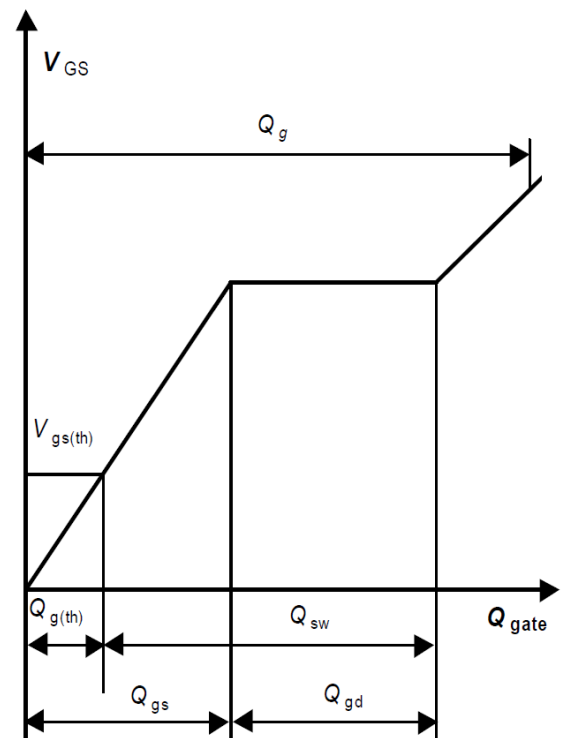
### 15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 100 \text{ A pulsed}$$

parameter:  $V_{DD}$



### 16 Gate charge waveforms



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**Edition 2023-06-15**

**Published by**

**Infineon Technologies AG**

**81726 Munich, Germany**

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## 修订记录

| Version | Date       | Changes                                                                        |
|---------|------------|--------------------------------------------------------------------------------|
| Rev 1.0 | 2008-02-11 | Final Data Sheet                                                               |
| Rev 1.1 | 2023-06-15 | Diagram 8 Typ. drain-source on-state resistance: used $\alpha$ value clarified |
| Rev 1.1 | 2023-06-15 | Corrected diagram 3 safe operating area                                        |
| Rev 1.1 | 2023-06-15 | Corrected diagram 10 typical capacitances                                      |



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版本 2026-09-29

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